MITSUBISHI LINEAR ICs

M5216

DUAL LARGE-CURRENT OPERATIONAL AMPLIFIERS (DUAL POWER SUPPLY TYPE)

DESCRIPTION

The M5216 is a semiconductor integrated circuit designed as a high-output and high-speed operational amplifier for use in high-performance headphone amplifiers and mixer amplifiers found in cassette decks.

The device comes in an 8-pin SIL or DIL package and it contains two circuits for yielding a high internally phasecompensated gain, a high current capacity and a high slew rate. It can be widely used as a general-purpose dual amplifier in electronic equipment. In addition, it can be used in a single power supply format and employed in conditions where the supply voltage is low. These are features which make this device ideal for headphone amplifiers in portable products.

FEATURES

- Large current capacity I_{LP} = ±100mA
- High power output······ P_o = 40mW(typ.)
 - $P_{\rm O} = 27 \rm mW(typ.)$
- High slew rate, high $f_T \cdot SR = 3.5V/us$, $f_T = 10MHz(typ.)$
- Low noise $(R_s = 1k\Omega)$ FLAT $V_{NI} = 1.7uVrms(typ.)$
- Low supply voltage drive possible \cdots $V_{cc} = 4V(\pm 2V)$
- High allowable power ··· Pd = 800mW(SIL), 625mW(DIL)

APPLICATION

High-performance headphone amplifiers in VTRs, tape decks and stereo cassette tape recorders with built-in radios; mixer amplifiers, public address equipment, electronic musical instruments; also as a high-current, high-speed, general-purpose operating amplifier in other electronic products and equipment.

RECOMMENDED OPERATING CONDITIONS

Supply voltage range $\pm 2V \sim \pm 16V$ (dual power supply) $+4V \sim +32V$ (single power supply) Rated supply voltage $\pm 15V$

APPLICATION EXAMPLE IN HEADPHONE AMPLIFIER



Note : For a single power supply system, the level of the (+) input pin should be shifted to $V_{\rm CC}/2$ potential and the output should be AC-coupled through a capacitor.







8-pin molded plastic DIL 8-pin molded plastic SIL





M5216

DUAL LARGE-CURRENT OPERATIONAL AMPLIFIERS (DUAL POWER SUPPLY TYPE)

ABSOLUTE MAXIMUM RATINGS $(T_a=25^{\circ}C, unless otherwise noted)$

Symbol	Parameter	Conditions	Limits	Unit	
V _{cc}	Supply voltage		±18	v	
I _{LP}	Load current		±100	mA	
Vid	Differential input voltage		±30	v	
Vic	Common input voltage		±15	v	
Pd	Power dissipation		800(M5216L)	mW	
			625(M5216P)		
Kθ	Thermal derating	T _a ≧25℃	8(M5216L)	mW/℃	
			6.25(M5216P)		
Topr	Ambient temperature		-20~+75	Ĉ	
T _{stg}	Storage temperature		-55~+125	ĉ	

ELECTRICAL CHARACTERISTICS $(T_a=25^{\circ}C, V_{cc}=\pm15V)$

Symbol	Parameter	Test conditions	Limits			
			Min	Тур	Мах	Unit
Icc	Circuit current	V _{IN} =0	-	7.5	12.0	mA
Vio	Input offset voltage	R _S ≦10kΩ	-	0.5	6.0	mV
lio	Input offset current		-	5	200	nA
I _{IB}	Input bias current		-		500	nA
Rin	Input resistance		0.3	5	-	MΩ
Gvo	Open loop voltage gain	$R_L \ge 2k\Omega$, $V_O = \pm 10V$	86	110	—	dB
V _{OM}	Maximum output voltage	$R_L \ge 2k\Omega$	±12	±13.5	. —	v
		R _L ≥150Ω	±10.5	±11	-	V
V _{CM}	Common input voltage width		±12	±14	—	v
CMRR	Common mode rejection ratio	R _S ≦10kΩ	70	90		dB
SVRR	Supply voltage rejection ratio	R _S ≦10kΩ		30	150	μV/V
Pd	Power dissipation		-	225	360	mW
SR	Slew rate	$G_V = 0 dB, R_L = 2k\Omega$	·	3.0		V/µs
f _⊤	Gain bandwidth product		-	10		MHz
VIN	Input referred noise voltage	$R_s=1k\Omega$, BW: 10Hz~30Hz	_	1.8	-	μVrms

TYPICAL CHARACTERISTICS



VOLTAGE GAIN VS FREQUENCY RESPONSE



